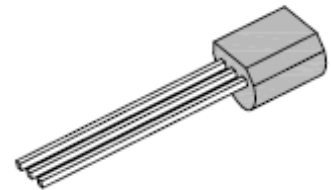
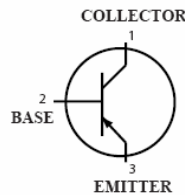


Small Signal General Purpose Transistors (PNP)

Features

- PNP Silicon Epitaxial Planar Transistor for Switching and Amplifier Applications
- RoHS compliance



TO-92



Mechanical Data

Case:	TO-92, Plastic Package
Terminals:	Solderable per MIL-STD-202G, Method 208
Weight:	0.18 gram

Maximum Ratings ($T_{Ambient}=25^{\circ}\text{C}$ unless noted otherwise)

Symbol	Description	BC327	BC328	Unit
V_{CEO}	Collector-Emitter Voltage	-45	-25	V
V_{CBO}	Collector-Base Voltage	-50	-30	V
V_{EBO}	Emitter-Base Voltage	-5.0		V
I_C	Collector Current-Continuous	800		mA
P_{tot}	Total Device Dissipation Alumina Substrate $T_A=25^{\circ}\text{C}$	625		mW/° C
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150		° C

Small Signal General Purpose Transistors (PNP)

BC327/BC328

Electrical Characteristics ($T_{Ambient}=25^{\circ}C$ unless noted otherwise)

Off Characteristics

Symbol	Description	BC327		BC328		Unit	Conditions
		Min.	Max.	Min.	Max.		
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	-45	-	-25	-	V	$I_C=-10mA, I_B=0$
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	-50	-	-30	-	V	$I_C=-100\mu A, I_E=0$
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	-5.0	-	-5.0	-	V	$I_C=-10\mu A, I_C=0$
I_{CEO}	Collector-Emitter Cut-off Current	-	-0.2	-	-0.2	μA	
		$V_{CE}=-40V, I_B=0$		$V_{CE}=-20V, I_B=0$			
I_{CBO}	Collector-Base Cut-off Current	-	-0.1	-	-0.1	μA	
		$V_{CB}=-45V, I_E=0$		$V_{CB}=-25V, I_E=0$			
I_{EBO}	Emitter-Base Cut-off Current	-	-0.1	-	-0.1	μA	$V_{EB}=-4V, I_C=0$

On Characteristics

Symbol	Description	BC327		BC328		Unit	Conditions
		Min.	Max.	Min.	Max.		
h_{FE1}	D.C. Current Gain	100	-	630	-		$V_{CE}=-1V, I_C=-100mA$
h_{FE2}		40	-	-	-		$V_{CE}=-1V, I_C=-300mA$
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	-	-0.7	-	-0.7	V	$I_C=-500mA, I_B=-5mA$
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	-	-1.2	-	-1.2	V	$I_C=-500mA, I_B=-5mA$
f_T	Transition Frequency	260	-	260	-	MHz	$V_{CE}=-5V, I_C=-10mA, f=100MHz$

h_{FE} Classification

Classification	16	25	40
h_{FE1}	100~250	160~400	250~630
h_{FE2}	60-	100-	170-

Small Signal General Purpose Transistors (PNP)

BC327/BC328

Typical Characteristics Curves

Fig.1- Static Characteristic

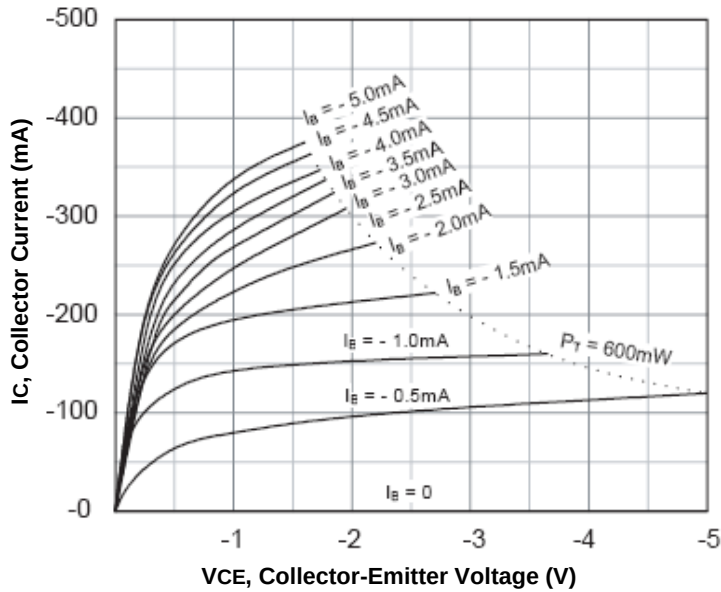


Fig.2- Static Characteristic

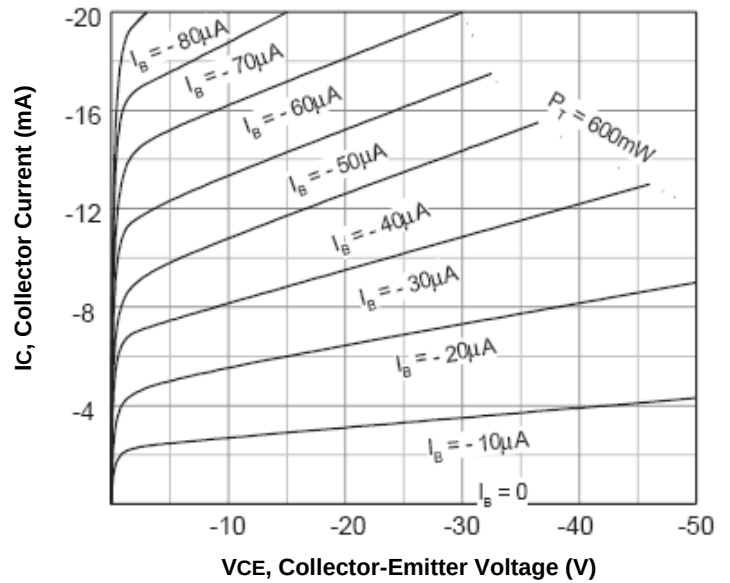


Fig.3- DC Current Gain

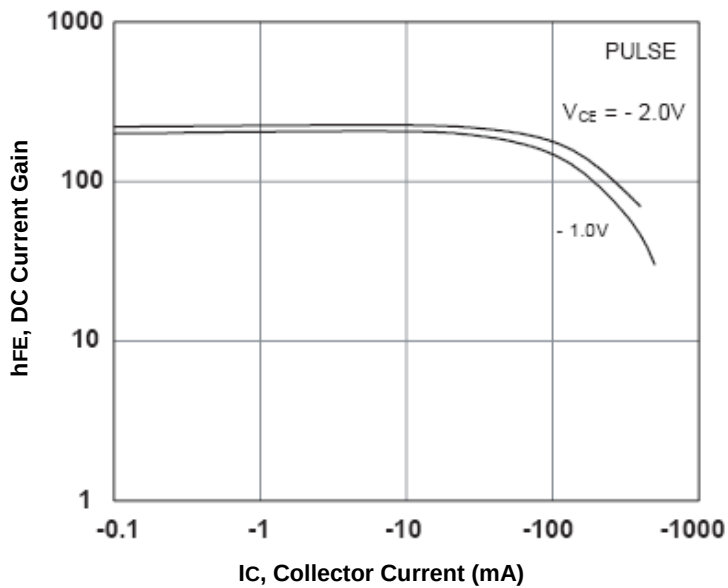
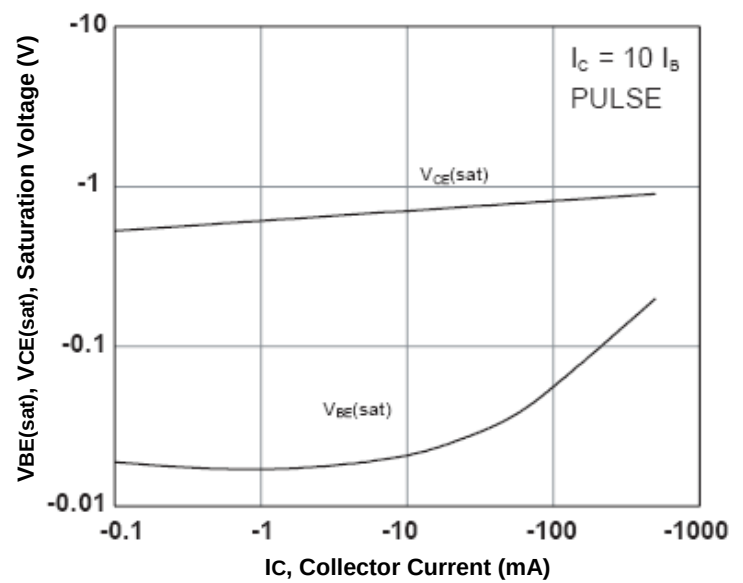


Fig.4- Base-Emitter Saturation Voltage
Collector -Emitter Saturation Voltage



Small Signal General Purpose Transistors (PNP)

BC327/BC328

Fig.5- Base-Emitter ON Voltages

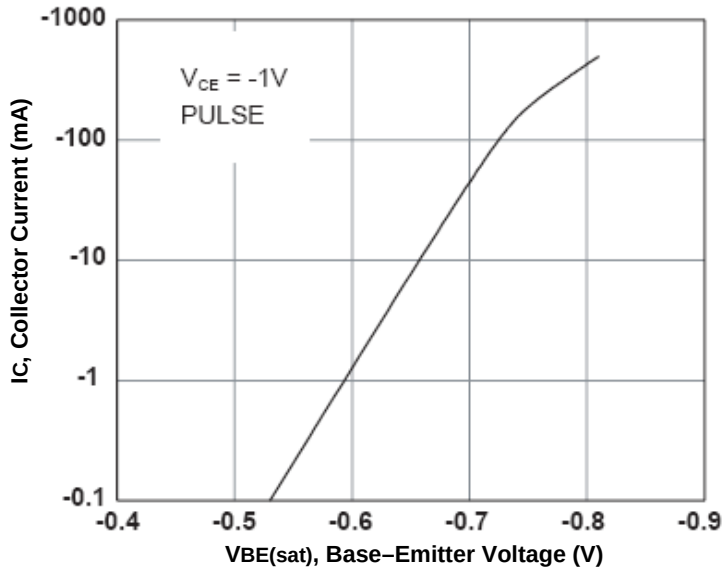
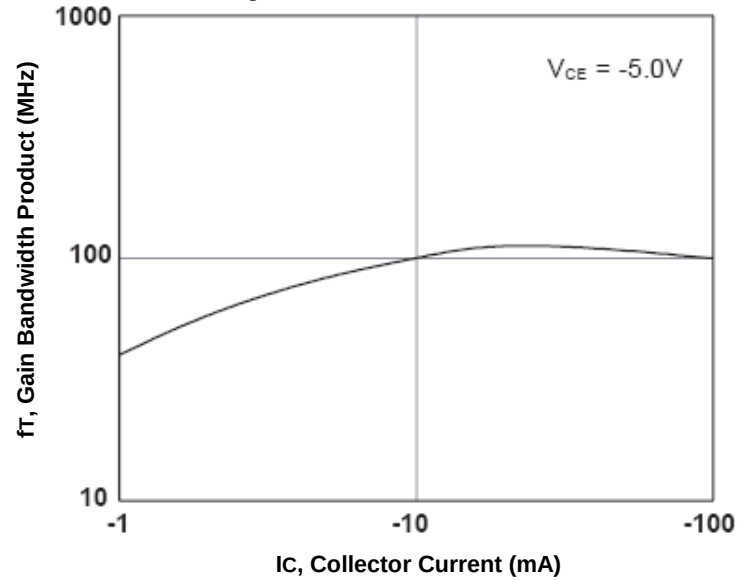
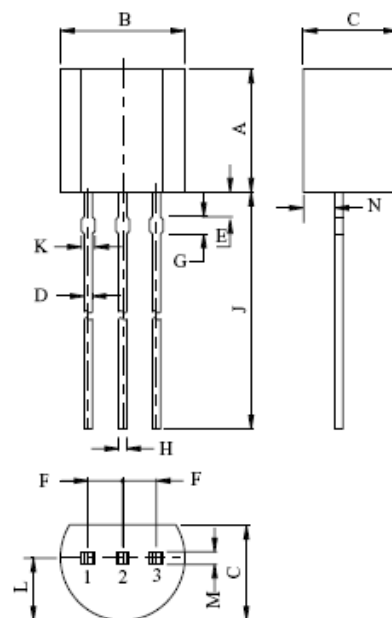


Fig.6- Gain Bandwidth Product



Dimensions in mm



DIM	MILLIMETERS
A	4.70 MAX
B	4.80 MAX
C	3.70 MAX
D	0.45
E	1.00
F	1.27
G	0.85
H	0.45
J	14.00±0.50
K	0.55 MAX
L	2.30
M	0.45 MAX
N	1.00

1. COLLECTOR
2. BASE
3. EMITTER

TO-92

TAITRON
components incorporated

Small Signal General Purpose Transistors (PNP)

BC327/BC328

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